

N-Channel Power MOSFET

Primary characteristics			
Symbol	Parameter	Value	Unit
I_D	Continuous drain current (@ $T_c=25^\circ\text{C}$)	4.0	A
V_{DS}	Drain-source voltage	30	V
R_{DSON}	Drain-source ON resistance (@ $V_{GS}=4.5\text{V}$)	<60	$\text{m}\Omega$

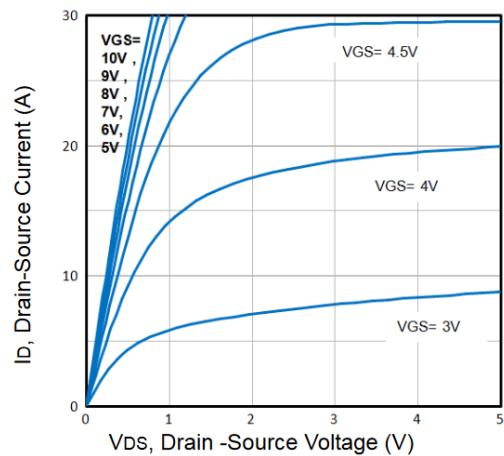
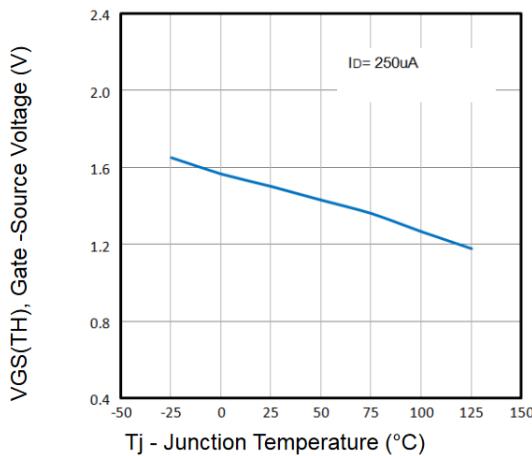
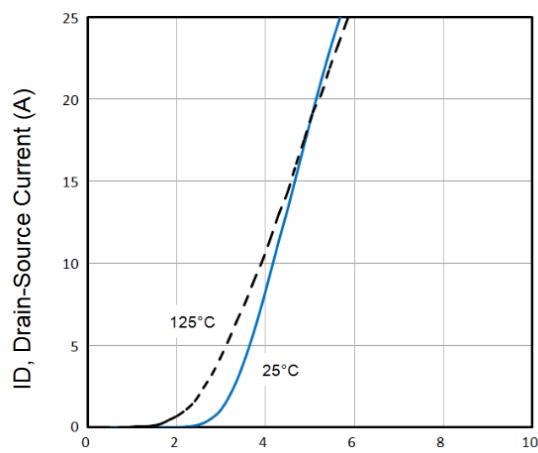
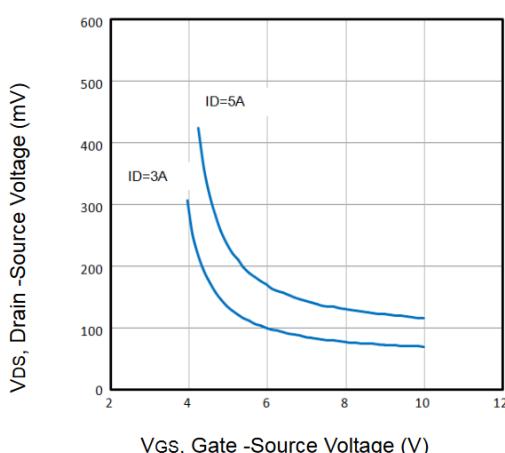
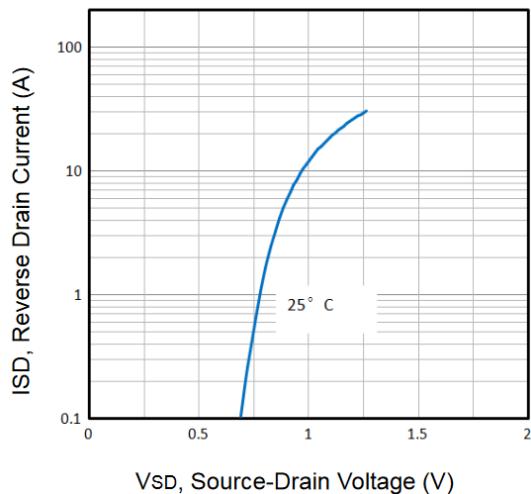
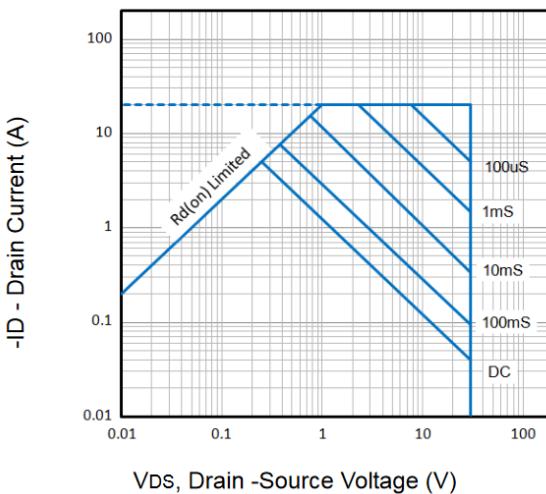
Case dimensions													
1 – Gate; 2 – Source; 3 – Drain													
SOT-23 (TO-236AB)													
Unit	A	$A_{1\max}$	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.0 ±0.1	0.1	0.43 ±0.05	0.12 ±0.03	2.9 ±0.1	1.3 ±0.1	1.9	0.95	2.3 ±0.2	0.3 ±0.15	0.5 ±0.05	0.2	0.1

Absolute maximum ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)								
Characteristic				Symbol	Value			Unit
Drain-source breakdown voltage				$V_{(BR)DS}$	30			V
Gate-source voltage				V_{GS}	±20			V
Continuous drain current	$V_{GS}=4.5\text{V}, T_A=25^\circ\text{C}$			I_D	4.0			A
	$V_{GS}=4.5\text{V}, T_A=70^\circ\text{C}$				3.2			
Pulse drain current tested ¹⁾	$T_A=25^\circ\text{C}$			I_{DM}	20.4			A
Maximum power dissipation	$T_A=25^\circ\text{C}$			P_D	1.5			W
	$T_A=70^\circ\text{C}$				0.9			
Thermal resistance junction-ambient				R_{eJA}	80 ~ 100			°C/W
Maximum junction temperature				T_J	150			°C
Operating junction temperature range				T_{STG}	-50 ~ 150			°C

Electrical characteristics ($T_J = 25^\circ\text{C}$)						
Characteristic	Test condition	Symbol	Min.	Value Typ.	Max.	Unit
Drain-source breakdown voltage	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$	$V_{(BR)DSS}$	30	-	-	V
Zero gate voltage drain current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$, $T_A=25^\circ\text{C}$	I_{DSS}	-	-	1.0	μA
	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$, $T_A=125^\circ\text{C}$		-	-	100	
Gate to body leakage current	$V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$	I_{GSS}	-	-	± 100	nA
Gate threshold voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	$V_{GS(\text{TH})}$	500	900	1500	mV
Drain-source ON-state resistance ²⁾	$V_{GS}=10\text{V}$, $I_D=4.0\text{A}$	$R_{DS(\text{ON})}$	-	29	50	$\text{m}\Omega$
	$V_{GS}=4.5\text{V}$, $I_D=3.0\text{A}$		-	44	60	
Dynamic electrical characteristics ($T_J = 25^\circ\text{C}$)						
Characteristic	Test condition	Symbol	Min.	Value Typ.	Max.	Unit
Input capacitance	$V_{DS}=24\text{V}$ $V_{GS}=0\text{V}$ $f=1.0\text{MHz}$	C_{iss}	-	300	-	pF
Output capacitance		C_{oss}	-	44	-	
Reverse transfer capacitance		C_{rss}	-	38	-	
Total gate charge	$V_{DS}=24\text{V}$ $V_{GS}=10\text{V}$ $I_D=2.0\text{A}$	Q_g	-	3.5	-	nC
Gate source charge		Q_{gs}	-	0.4	-	
Gate drain ("Miller") charge		Q_{gd}	-	1.7	-	
Switching characteristics						
Characteristic	Test condition	Symbol	Min.	Value Typ.	Max.	Unit
Turn on delay time	$V_{DD}=24\text{V}$ $I_D=5.0\text{V}$ $R_G=3.3\Omega$ $V_{GS}=10\text{V}$	$t_{d(on)}$	-	2.2	-	ns
Turn on rise time		t_r	-	6.9	-	
Turn off delay time		$t_{d(off)}$	-	15.5	-	
Turn off fall time		t_f	-	4.5	-	
Source drain diode characteristics						
Characteristic	Test condition	Symbol	Min.	Value Typ.	Max.	Unit
Source drain current (body diode)	$T_A=25^\circ\text{C}$	I_{SD}	-	-	1.8	A
Forward ON-voltage ²⁾	$I_{SD}=5.0\text{A}$, $V_{GS}=0\text{V}$, $T_J=25^\circ\text{C}$	V_{SD}	-	-	1.2	V

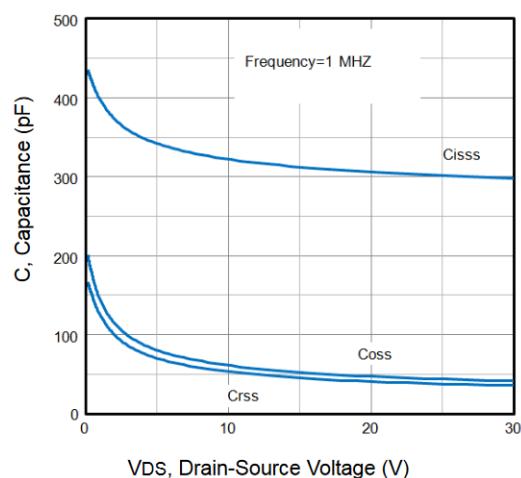
Notes:

- 1) Pulse width limited by maximum allowable junction temperature
- 2) Pulse test; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

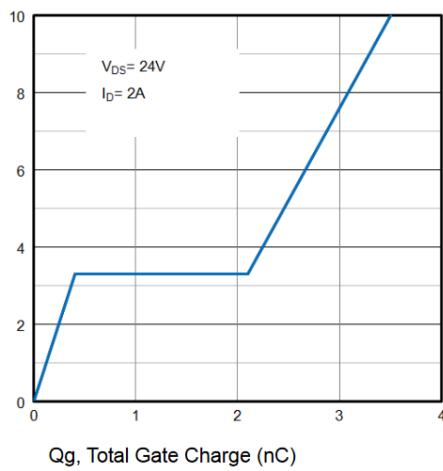
Typical characteristics
Output characteristics

Normalized threshold voltage vs. temperature

Transfer characteristics

Drain-source voltage vs. gate-source voltage

Typical source-drain diode forward voltage

Maximum safe operating area


Typical characteristics

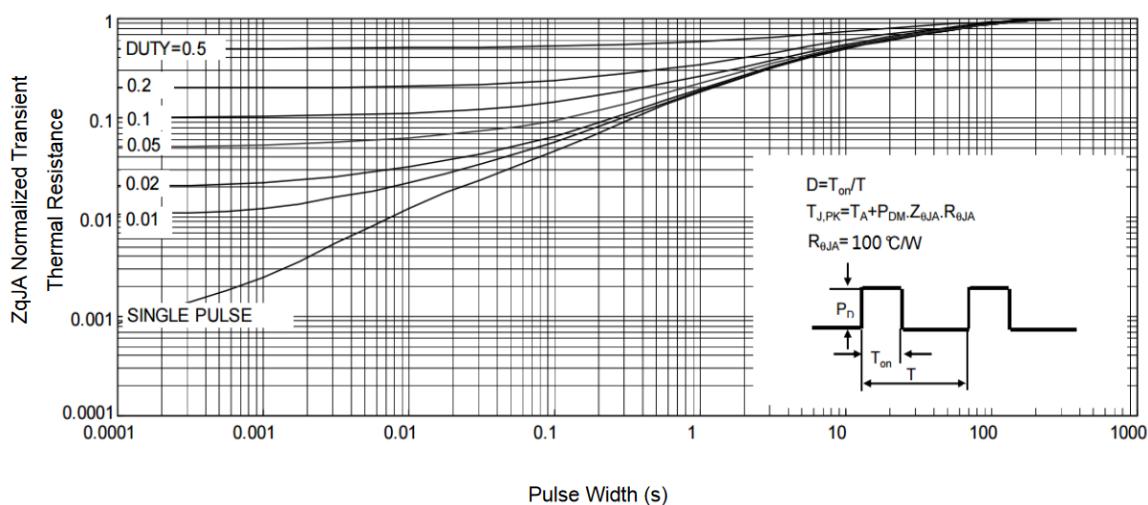
Typical capacitance vs. drain source voltage



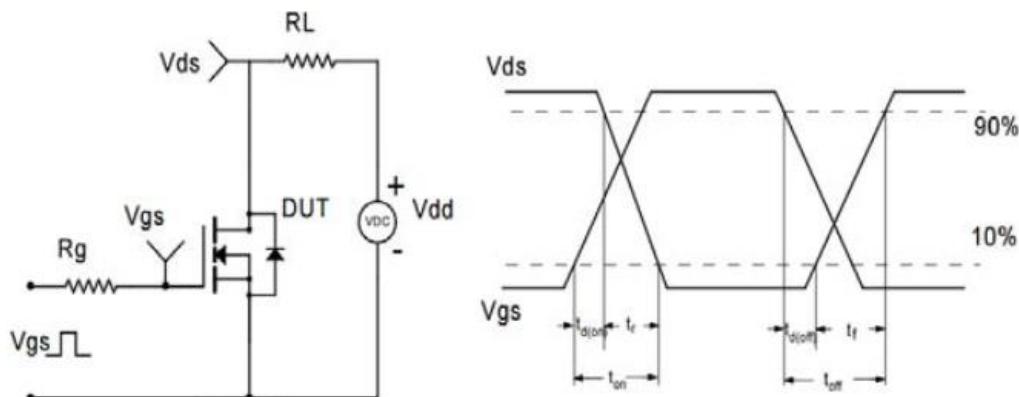
Typical gate charge vs. gate-source voltage



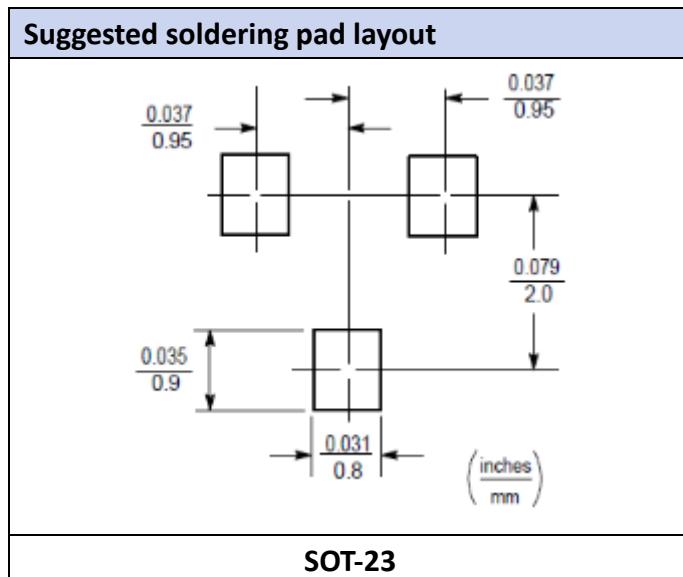
Normalized maximum transient thermal impedance



Switching time test circuit and waveforms



Ordering information		
Part Number	Package	Shipping Quantity
AKS3402	SOT-23	3000 pcs / reel



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